

Typical Applications

- Communications
- Electronic Warfare
- Test Instrumentation
- EMC Amplifier

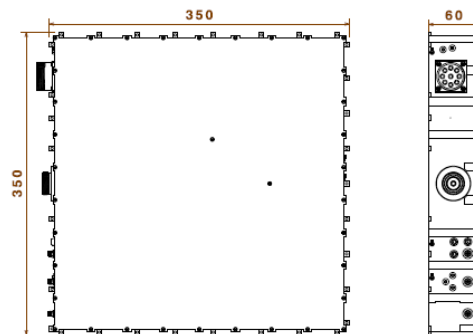
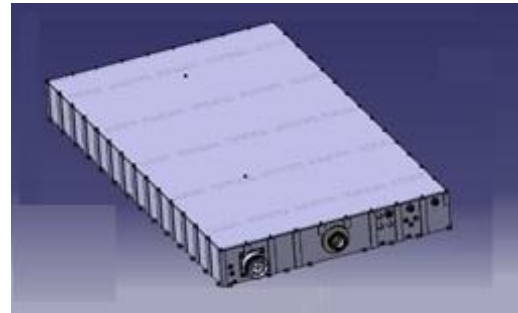
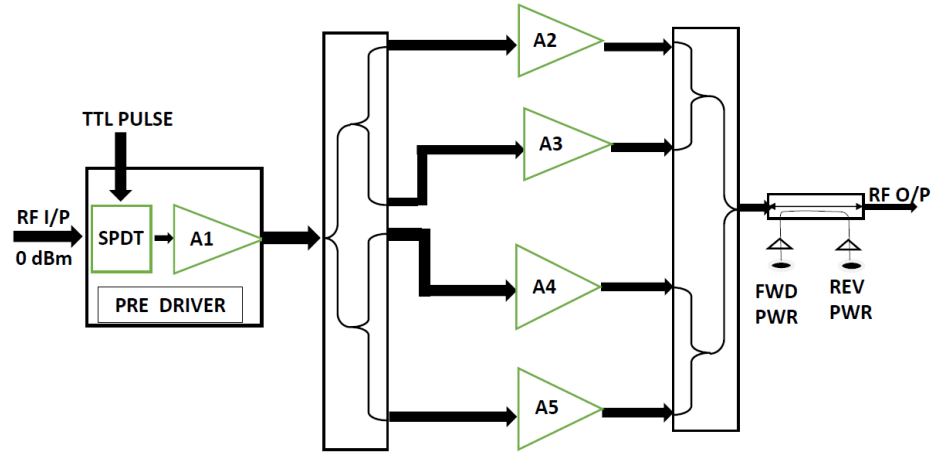
Features

- 2.0 to 6.0 GHz
- 50 dB Power Gain
- Psat : +50 dBm
- +28 V Supply
- Power Added Efficiency : 20%
- Compact Modular Housing

General Description

The ATPL-SSPA2060-100W is a wideband solid state power amplifier using GaN on SiC technology, operating from 2.0 to 6.0 GHz and offers 100 W saturated output power, greater than 20% power added efficiency and 50 dB Power Gain. The architecture is based on paralleling of four 45 W gain blocks and is ideally suited to support a variety of commercial and defence related applications.

100 W GaN Based CW Power Amplifier



Electrical Specifications (at 25°C)

Operating Frequency Range	2.0 to 6.0 GHz
Saturated Power Output	100 W CW (Min.)
Power Gain	50 dB
Pulse Modulation Capability	TTL on/off, TTL '1' for CW
Input & Output Return Loss	8 dB Min.
Harmonics (2 nd & 3 rd)	Better than 12 dB
Output Mismatch Protection	Provision of Reflected Power Sense For Output VSWR > 2:1
Operating Voltage	+28 V DC Supply
Power Consumption	+28 V, 20 Amps. (Max.)
Operating Temperature	0°C to +50°C
Power Added Efficiency	20%
RF Connectors	Input – SMA (Female), Output – N (Female)
Size	350 mm (W) × 350 mm (L) × 60 mm (H) Max. Without Cold Plate / Heat Sink
Cooling	Through Base Plate Designed For Proper Heat Transfer